
2SC4742

Silicon NPN Triple Diffused

HITACHI

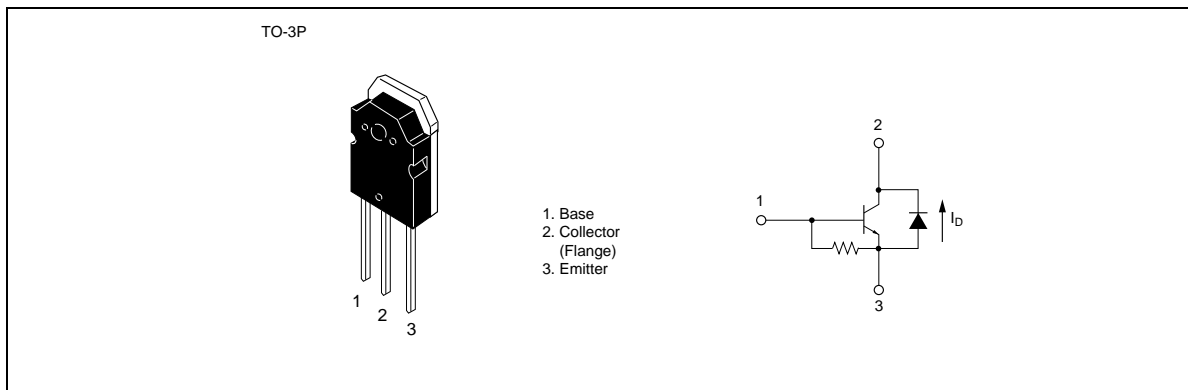
Application

Character display horizontal deflection output

Feature

- High breakdown voltage
 $V_{CES} = 1500 \text{ V}$
- Built-in damper diode type

Outline



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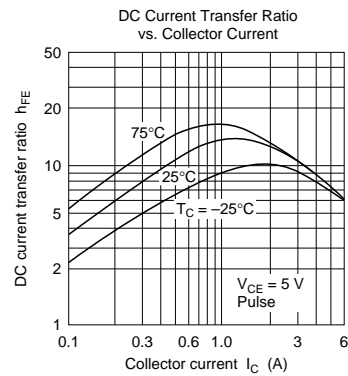
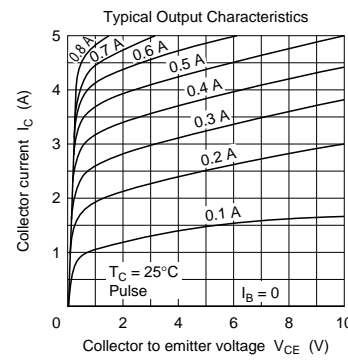
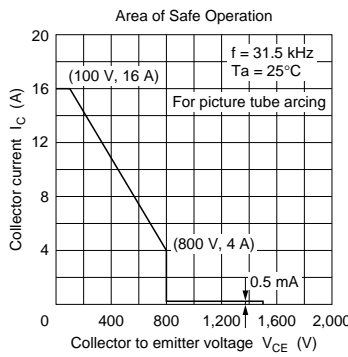
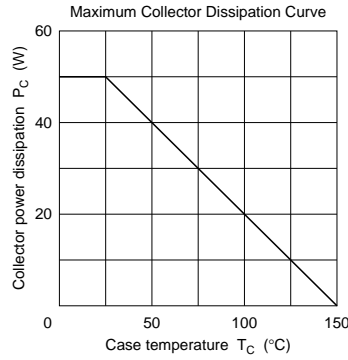
Absolute Maximum Ratings (Ta = 25°C)

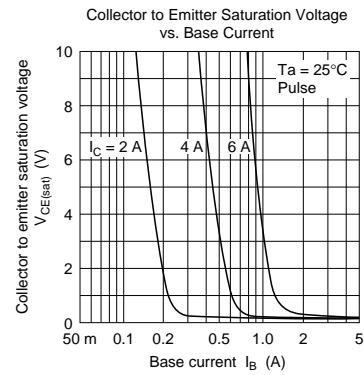
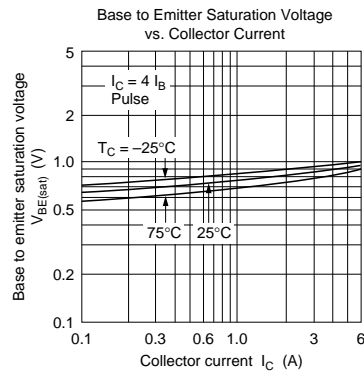
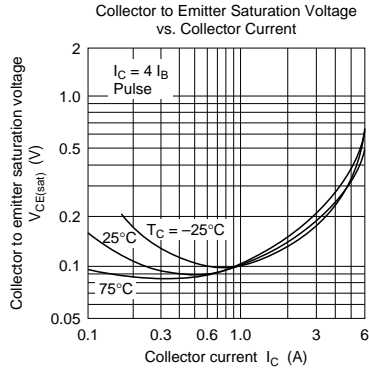
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	1500	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	6	A
Collector peak current	$I_{C(peak)}$	7	A
Collector surge current	$I_{C(surge)}$	16	A
Collector power dissipation	P_C^{*1}	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
C to E diode forward current	I_D	7	A

Note: 1. Value at $T_C = 25^\circ\text{C}$.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 400\text{ mA}, I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{ V}, R_{BE} = 0$
DC current transfer ratio	h_{FE}	—	—	25		$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	2.0	V	$I_C = 5\text{ A}, I_B = 1.25\text{ A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 5\text{ A}, I_B = 1.25\text{ A}$
C to E diode forward voltage	V_{ECF}	—	—	2.0	V	$I_F = 6\text{ A}$
Fall time	t_f	—	—	0.4	μs	$I_{CP} = 5\text{ A}, I_{B1} = 1\text{ A}, I_{B2} = -2\text{ A}$





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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071